

PTO-1449 REPRODUCED		ATTORNEY DOCKET NO. 2037.2038-001	APPLICATION NO. 10/647,664
INFORMATION DISCLOSURE CITATION IN AN APPLICATION		FIRST NAMED INVENTOR Tony Mai	FILING DATE August 25, 2003
January 9, 2004 (Use several sheets if necessary)		EXAMINER	CONFIRMATION NO. 2135
			GROUP 2631

JAN 23 2004
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U.S. PATENT DOCUMENTS				
EXAMINER INITIAL	REF. NO.	DOCUMENT NUMBER Number-Kind Code (if known)	ISSUE DATE / PUBLICATION DATE MM-DD-YYYY	NAME OF PATENTEE OR APPLICANT OF CITED DOCUMENT
EB	AA	6,314,052 B2	11/06/01	Foss <i>et al.</i>
EB	AB	6,314,150 B1	11/06/01	Vowe
EB	AC	6,330,296 B1	12/11/01	Atallah <i>et al.</i>
EB	AD	6,337,590 B1	01/08/02	Miller
EB	AE	6,448,820 B1	09/10/02	Wang <i>et al.</i>
EB	AF	6,549,041 B2	04/15/03	Waldrop
	AG			
	AH			
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	AA3			
	AB3			
	AC3			

EXAMINER <i>/Emmanuel Bayard/ (10/04/2006)</i>	DATE CONSIDERED
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EB	AR	C.H. Kim <i>et al.</i> "A 64 Mbit, 640 Mbyte/s bidirectional Data Strobed, Double-Data-Rate SDRAM with a 40-mW DLL for a 256-Mbyte System", <i>IEEE J. Solid State Circuits</i> , 33(11), November 1998.	
EB	AS	Hsiang-Hui Chang <i>et al.</i> "A Wide Range Delay-Locked Loop With a Fixed Latency of One Clock Cycle", <i>IEEE J. Solid State Circuits</i> , 37(8), August 2002.	
EB	AT	Hongil Yoon <i>et al.</i> "A 2.5V, 333-Mb/s/pin, 1-Gbit, Double-Data-Rate Synchronous DRAM", <i>IEEE J. Solid State Circuits</i> , 34(11), November 1999.	
EB	AU	Se Jun Kim, <i>et al.</i> "A low-Jitter Wide-Range Skew-Calibrated Dual-Loop DLL Using Antifuse Circuitry for High-Speed DRAM", <i>IEEE J. Solid State Circuits</i> , 37(6), June 2002.	
	AV		
	AW		
	AX		
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	AR2		
	AS2		
	AT2		
	AU2		
	AV2		
	AW2		
	AX2		

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<p>PTO-1449 REPRODUCED</p> <p><i>P.E.</i></p> <p><i>JAN 24 2005</i></p> <p><i>SEARCHED</i></p> <p>INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION</p> <p>January 19, 2005</p> <p>(Use several sheets if necessary)</p>	ATTORNEY DOCKET NO. 2037.2038-001	APPLICATION NO. 10/647,664
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U.S. PATENT DOCUMENTS

CITED DOCUMENTS				
EXAM- INER INITIAL	REF. NO.	DOCUMENT NUMBER Number-Kind Code (if known)	ISSUE DATE / MM-DD-YYYY	NAME OF PATENTEE OF CITED DOCUMENT
EB	AG	6,239,634 B1	05-29-2001	McDonagh

U.S. PUBLISHED APPLICATIONS

EXAMINER	/Emmanuel Bayard/ (10/04/2006)	DATE CONSIDERED
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